

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

MS8002B

Product specification

概述

MS8002B是一颗单通道 AB 类差分输入音频功率放大器。在 5.0V 电源供电，THD+N=10%，3 欧姆负载上可以输出 2.8W 的功率。

MS8002B的差分输入架构能有效提高噪声的抑制能力。产品应用电路简单，仅需极少数的外围器件，就能提供高品质低失真的输出。

MS8002B具有关断功能，极大的延长系统的待机时间。过热保护功能增强系统的可靠性。POP 声抑制功能改善了系统的听觉感受，同时简化系统调试。

MS8002B提供 SOP8 封装

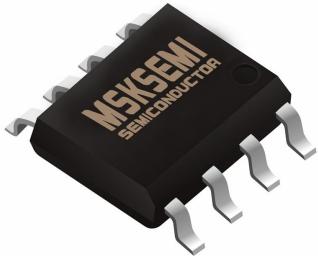
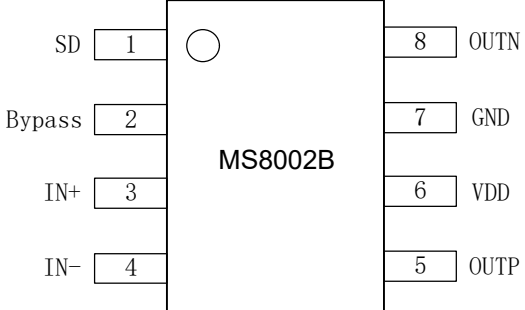
特性

- 输出功率：
 - 1.6W (VDD=5.0V, $R_L=8\Omega$, THD+N=10%)
 - 2.6W (VDD=5.0V, $R_L=4\Omega$, THD+N=10%)
 - 2.8W (VDD=5.0V, $R_L=3\Omega$, THD+N=10%)
- 工作电压：2.5V to 5.5V
- 低失真和低噪声
- 开机 POP 声抑制功能
- 过热保护功能

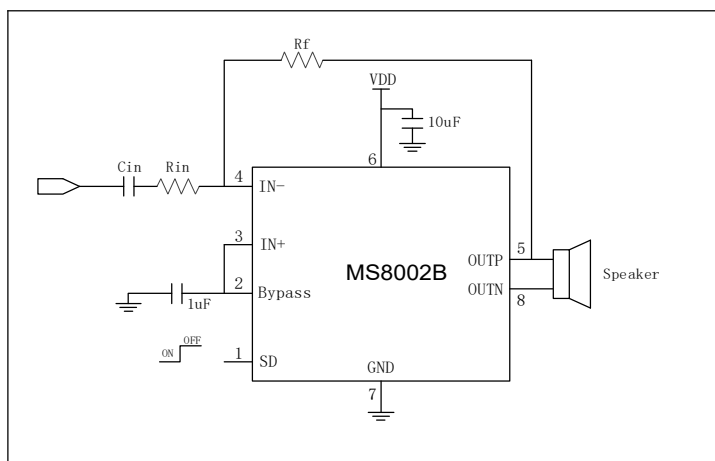
应用

- FM 播放器
- 网络摄像头
- 玩具及游戏机
- 插卡音箱/USB 音箱/蓝牙音箱

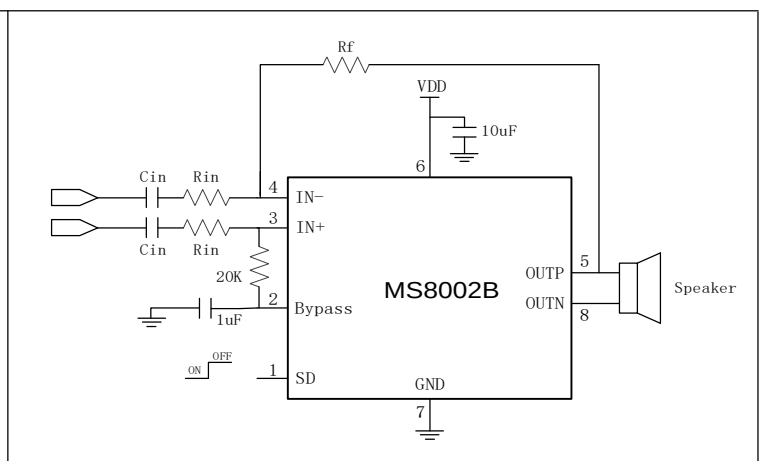
引脚描述和标记

SOP-8	引脚说明	管体标记
	 SD 1 Bypass 2 IN+ 3 IN- 4 8 OUTN 7 GND 6 VDD 5 OUTP	 MSKSEMI MS8002B MS**

单端输入典型应用电路图



差分输入典型应用电路图



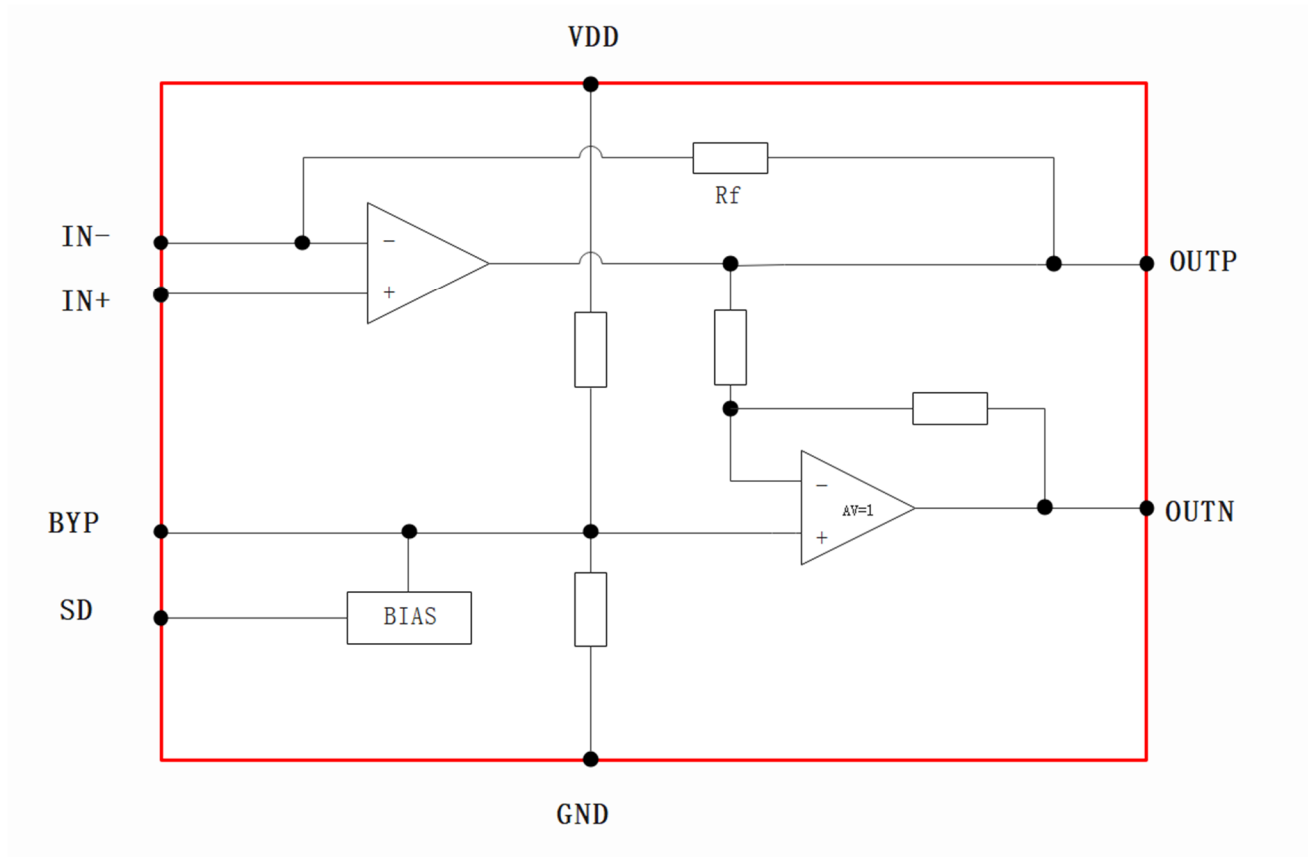
管脚描述

管脚	符号	I/O	描述
1	SD	I	系统关断控制，默认高电平（高电平关机，低电平工作）
2	Bypass	I	参考电压
3	IN+	I	音频正输入端
4	IN-	I	音频负输入端
5	OUTP	O	音频正输出端口
6	VDD	P	电源
7	GND		地
8	OUTN	O	音频负输出端口

订货信息

料号	封装	包装
MS8002B	SOP8	4000颗/盘

功能框图



绝对最大额定值

V _{DD}	供电电压	-0.3V to 6V
V _I	输入电压	-0.3V to V _{DD} +0.3V
T _A	工作温度	-40°C to 85°C
T _J	结温	-40°C to 125°C
T _{STG}	储存温度	-65°C to 150°C
T _{SLD}	焊接温度	300°C, 5sec

注：绝对最大额定值是指设备的寿命受到损害的值，在绝对最大额定条件下会引起芯片的永久性损坏。

推荐额定值

			MIN	MAX	UNIT
V _{DD}	供电电压	VDD	2.5	5.5	V
V _{IH}	SD高电平	V _{DD} =5.0V	2		V
V _{IL}	SD低电平	V _{DD} =5.0V		0.6	V
RL _{MIN}	最小负载	V _{DD} =5.0V	3		Ω

热阻参数

Parameter	Symbol	Package	MAX	UNIT
热阻(Junction to Ambient)	θ _{JA}	SOP8	115	°C/W
热阻 (Junction to Case)	θ _{JC}		63	°C/W

电性参数

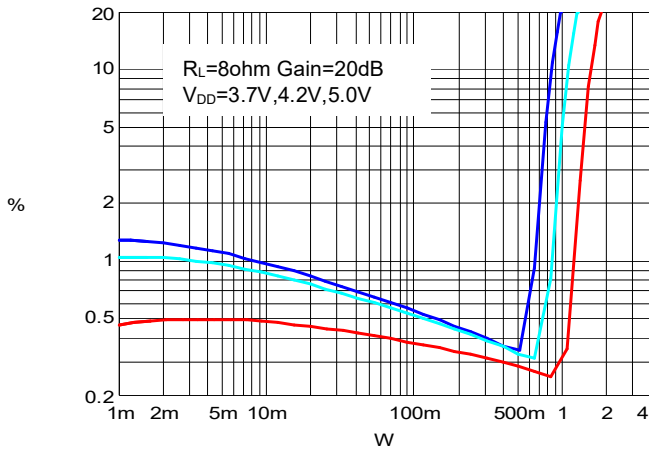
(VDD =5V, Gain=20dB, RL =8Ω, T =25°C, unless otherwise noted.)

Symbol	Parameter	Test Conditions		MIN	TYP	MAX	UNIT
Po	输出功率	THD+N=10%,f=1KHZ,RL=8Ω	VDD=5.0V		1.6		W
			VDD=4.2V		1.1		
			VDD=3.7V		0.85		
		THD+N=1%, f=1KHZ,RL=8Ω	VDD=5.0V		1.3		W
			VDD=4.2V		0.86		
			VDD=3.7V		0.66		
		THD+N=10%,f=1KHZ,RL=4Ω	VDD=5.0V		2.6		W
			VDD=4.2V		1.7		
			VDD=3.7V		1.3		
		THD+N=1%, f=1KHZ,RL=4Ω	VDD=5.0V		2.0		W
			VDD=4.2V		1.3		
			VDD=3.7V		1.0		
THD+N	总谐波失真 + 噪声	VDD=5.0V, Po=1.0W, RL=8Ω VDD=3.7V, Po=0.5W, RL=8Ω	f=1KHz		0.3		%
					0.4		
Gv	增益	Rin=27K, Ri=150K	VDD=3.7V		20		dB
PSRR	电源纹波抑制比	VDD=4.2V ±200mVp-p	f=1KHz		57		dB
SNR	信噪比	VDD=5.0V, Vorms=1V, Gv=20dB	f=1KHz		89		dB
Vn	残余噪声	VDD=5.0V, Input floating with Cin=0.1μF	A-weighting		35		μV
			No A-weighting		53		
Dyn	动态范围	VDD=5.0V, THD=1%	f=1KHz		98		dB
Iq	静态电流	VDD=5.0V	VSD=0.3V No Load		5		mA
		VDD=4.2V			4		
		VDD=3.7V			3		
ISD	关断电流	VDD=2.0V to 5.0V	VSD=3.3V		1		μA
Vos	失调电压	VDD=5V, AC_GND			3		mV
Tst	启动时间	CBy = 1.0uF			90		mS
OTP	温度保护	Junction Temperature, No Load	VDD=5.0V		175		°C
OTH	迟滞温度				30		

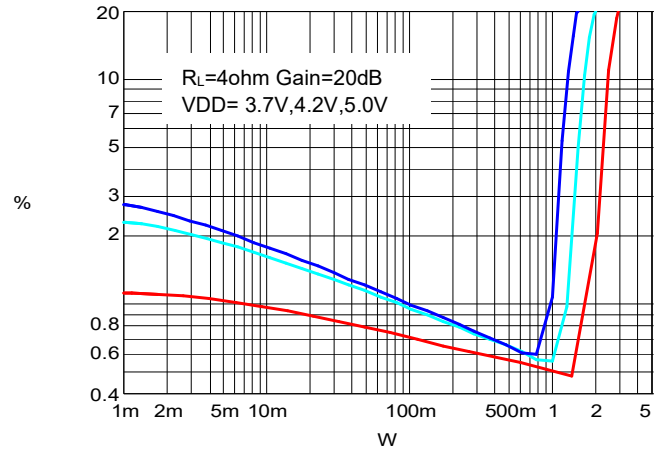
典型特征曲线

(VDD = 5V, Gain=20dB, $R_L = 8\Omega$, T = 25°C, unless otherwise noted.)

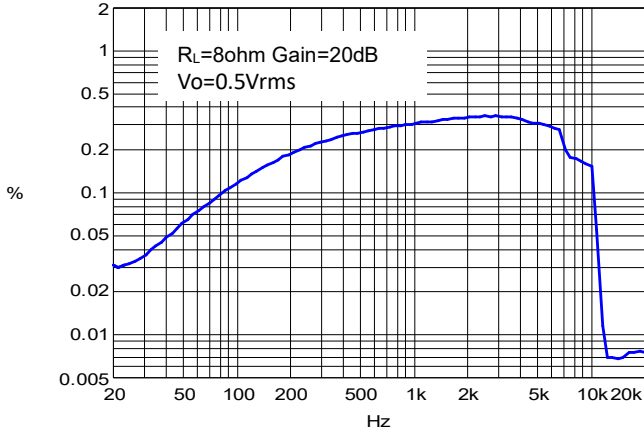
THD+N vs Output Power



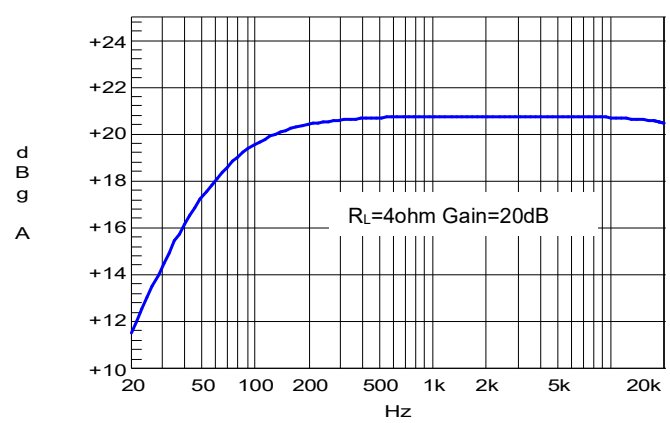
THD+N vs Output Power



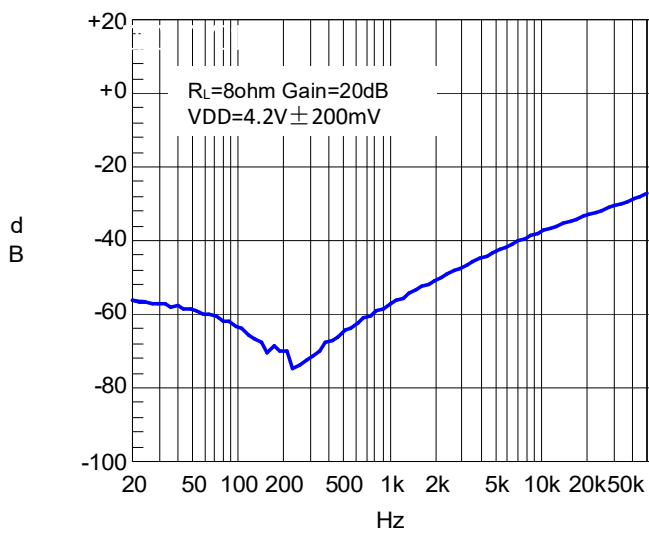
THD+N VS Frequency



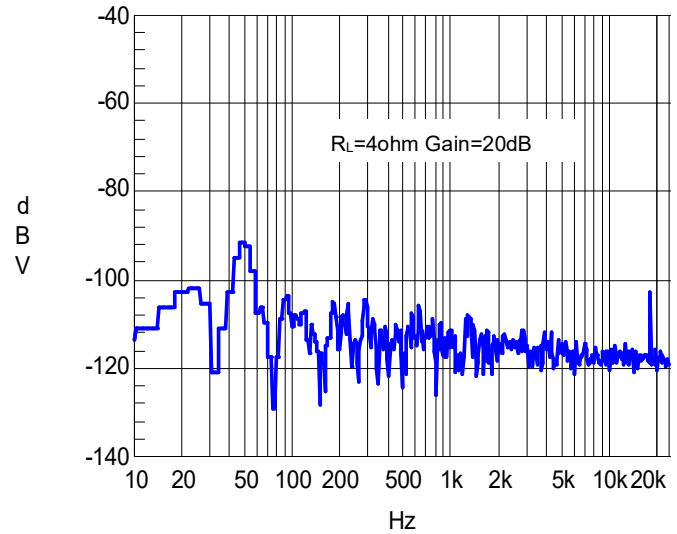
Frequency Response



PSRR



Noise Floor FFT



应用信息

输入电阻(Ri)

MS8002B 的增益由音量调节控制的输入电阻(RI)和反馈电阻(RF)控制。

增益计算如下：

$$A_v = 2 \times \frac{R_f}{R_i} \left(\frac{V}{V} \right)$$

其中，输入电阻RI为外部的输入电阻，Rf为外部反馈电阻。

输入电容 (Ci)

输入电容与输入电阻构成一个高通滤波器，其截至频率可由下式得出：

$$f_c = \frac{1}{(2\pi R_i C_i)}$$

Ci的值不仅会影响到电路的低频响应，而且也会影响电路启动和关断时所产生的POP声，输入电容越大，则到达其稳定工作点所需的电荷越多，在同等条件下，小的输入电容所产生的POP声比较小。

偏置电容CBYP

偏置电容是最关键的电容，它与几个重要性能相关，当电路启动时，偏置电容决定了放大器的开启速度，偏置电容同时会影响到电路的噪声和电源抑制比以及开关机的POP声。

为避免启动时的POP声，偏置电压的上升速度应该比输入偏置电压的上升速度慢。

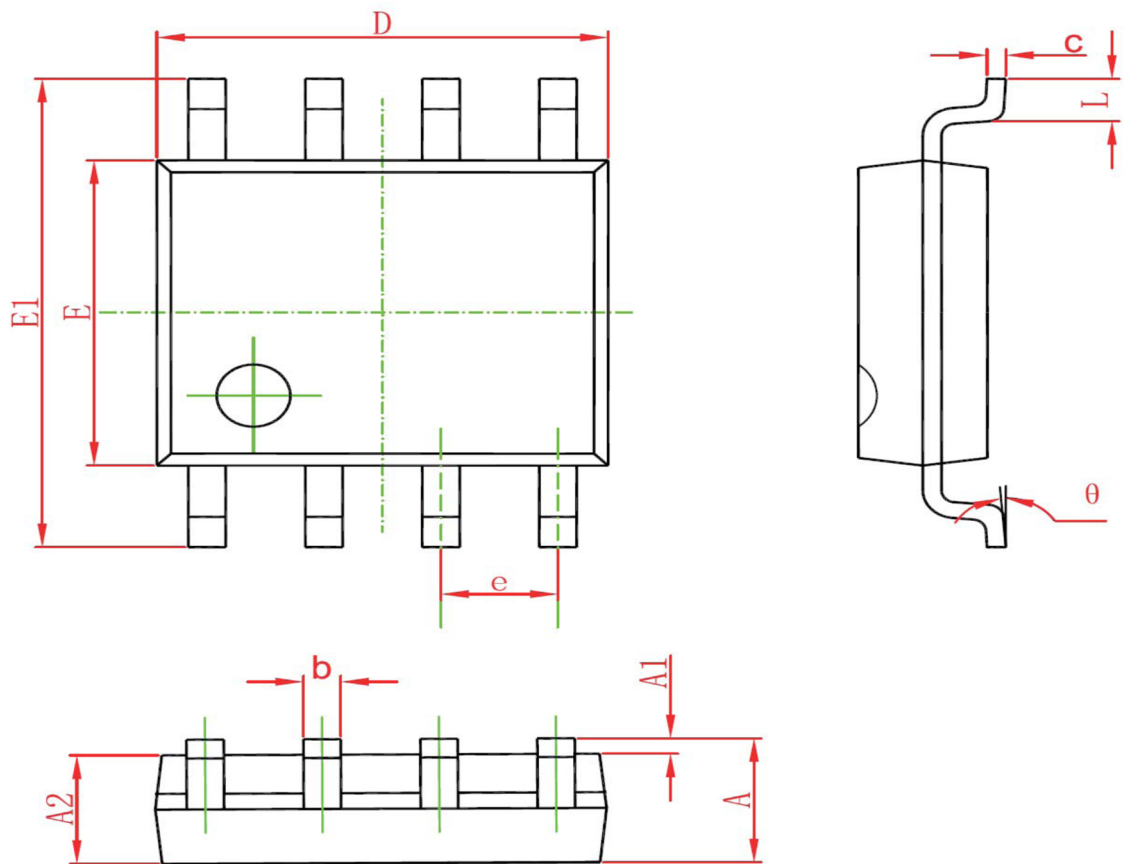
关断工作模式

为了减少在关断模式下的功率损耗，MS8002B 带有关闭放大器偏置的关断电路。当SD引脚为低电平时，放大器正常工作。当SD引脚为高电平时，放大器被关闭，工作电流达到最小；SD引脚默认高电平。

过温保护

MS8002B带有过温保护电路以防止内部温度超过175℃时器件损坏。在不同器件之间，这个值有25℃的差异。当内部电路超过设置的保护温度时，器件进入关断状态，输出被截止。当温度下降 30℃后，器件重新正常工作。

封装图（SOP8）



符号	毫米（mm）		英寸（Inch）	
	最小值	最大值	最小值	最大值
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	1.550	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.27(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050

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